

B' *und*
adjacent the gate sidewall spacers, which conductive layer adjacent the gate sidewall spacers serves as a source/drain region.--

IN THE CLAIMS

Please substitute the following clean copy text for the pending claims of the same number:

- SubC-1
- B2
Sub
F1
15. (Amended) A thin film transistor structure, comprising:
an insulating substrate,
a polysilicon layer over the substrate;
a gate structure over the polysilicon layer, wherein the gate structure includes a gate layer,
a gate dielectric layer between the gate layer and the polysilicon layer and a spacer on each side
of the gate layer; and
a conductive layer over the gate layer and the polysilicon layer adjacent to the spacers,
wherein the conductive layer adjacent to the spacers serves as a source/drain region.
17. (Amended) The structure of claim 15, wherein the conductive layer comprises an in-
situ doped silicon-germanium (SiGe) layer.
18. (Amended) The structure of claim 15, wherein the conductive layer comprises a
tungsten layer.
19. (Amended) The structure of claim 15, wherein the conductive layer comprises a metal
silicide layer.
20. (Amended) The structure of claim 15, wherein the spacer comprises a tetra-ethyl-
ortho-silicate (TEOS) layer.